

# **Darlington Power Transistors**

### **DPAK For Surface Mount Applications**

# **MJD6039, NJVMJD6039T4G**

Designed for general purpose power and switching such as output or driver stages in applications such as switching regulators, convertors, and power amplifiers.

#### **Features**

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Monolithic Construction With Built-in Base-Emitter Shunt Resistors
- High DC Current Gain  $h_{FE} = 2500$  (Typ) @  $I_C = 4.0$  Adc
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings:
  - Human Body Model, 3B > 8000 V
  - Machine Model, C > 400 V
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Pb-Free Package is Available\*

#### **MAXIMUM RATINGS**

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	80	Vdc
Collector-Base Voltage	V <sub>CB</sub>	80	Vdc
Emitter-Base Voltage	V <sub>EB</sub>	5	Vdc
Collector Current Continuous Peak	I <sub>C</sub>	4 8	Adc
Base Current	Ι <sub>Β</sub>	100	mAdc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	20 0.16	W W/°C
Total Power Dissipation (Note 2) @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

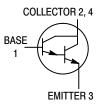
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

These ratings are applicable when surface mounted on the minimum pad sizes recommended.

# SILICON POWER TRANSISTORS 4 AMPERES, 80 VOLTS, 20 WATTS



DPAK CASE 369C STYLE 1



#### **MARKING DIAGRAM**



A = Assembly Location

Y = Year
WW = Work Week
J6039 = Device Code
G = Pb-Free Package

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MJD6039T4G	DPAK (Pb-Free)	2500 / Tape & Reel
NJVMJD6039T4G	DPAK (Pb-Free)	2500 / Tape & Reel

#### **DISCONTINUED** (Note 1)

	1	i
MJD6039T4	DPAK	2500 /
	(Pb-Free)	Tape & Reel

- †For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
- DISCONTINUED: This device is not recommended for new design. Please contact your onsemi representative for information. The most current information on this device may be available on <a href="https://www.onsemi.com">www.onsemi.com</a>.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **MJD6039, NJVMJD6039T4G**

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 3)	$R_{ heta JA}$	71.4	°C/W

<sup>3.</sup> These ratings are applicable when surface mounted on the minimum pad sizes recommended.

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

,				
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	80	-	Vdc
Collector–Cutoff Current $(V_{CE} = 40 \text{ Vdc}, I_B = 0)$	I <sub>CEO</sub>	-	10	μAdc
ON CHARACTERISTICS (Note 4)				
DC Current Gain $(I_C = 1 \text{ Adc}, V_{CE} = 4 \text{ Vdc})$ $(I_C = 2 \text{ Adc}, V_{CE} = 4 \text{ Vdc})$	h <sub>FE</sub>	1000 500	- -	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 2 Adc, I <sub>B</sub> = 8 mAdc)	V <sub>CE(sat)</sub>	-	2.5	Vdc
Base-Emitter On Voltage (I <sub>C</sub> = 2 Adc, V <sub>CE</sub> = 4 Vdc)	V <sub>BE(on)</sub>	-	2.8	Vdc
DYNAMIC CHARACTERISTICS				
Small-Signal Current Gain (I <sub>C</sub> = 0.75 Adc, V <sub>CE</sub> = 10 Vdc, f = 1 kHz)	h <sub>fe</sub>	25	-	-
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 0.1 MHz)	C <sub>ob</sub>	-	100	pF

<sup>4.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%.

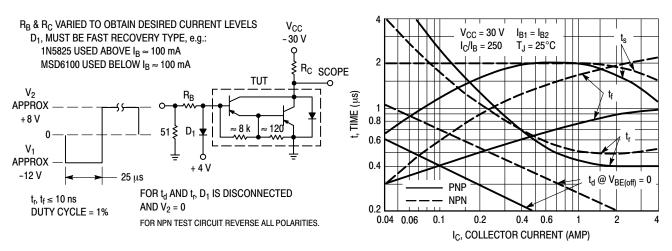


Figure 1. Switching Times Test Circuit

Figure 2. Switching Times

#### **MJD6039, NJVMJD6039T4G**

#### TYPICAL ELECTRICAL CHARACTERISTICS

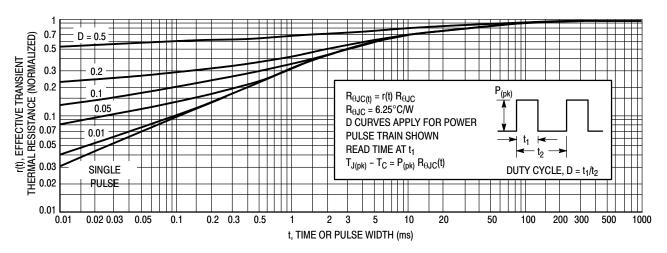


Figure 3. Thermal Response

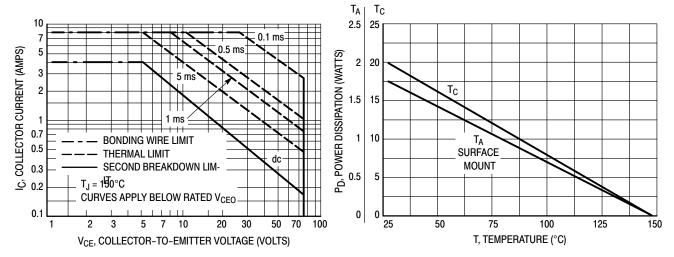


Figure 4. Maximum Rated Forward Biased Safe Operating Area

Figure 5. Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 6 and 7 is based on  $T_{J(pk)} = 150^{\circ} C$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} < 150^{\circ} C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

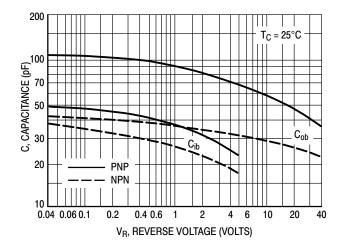


Figure 6. Capacitance

#### **MJD6039, NJVMJD6039T4G**

#### TYPICAL ELECTRICAL CHARACTERISTICS

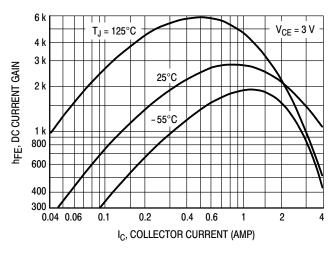


Figure 7. DC Current Gain

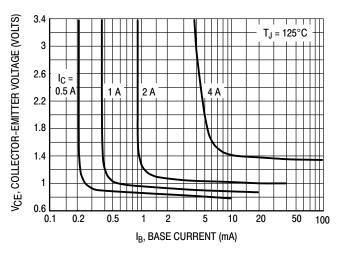


Figure 8. Collector Saturation Region

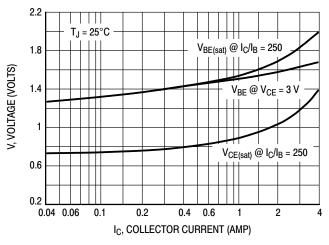


Figure 9. "On" Voltages

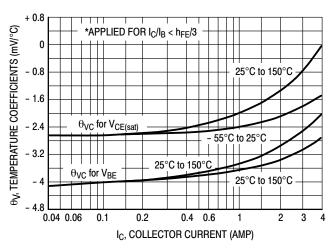


Figure 10. Temperature Coefficients

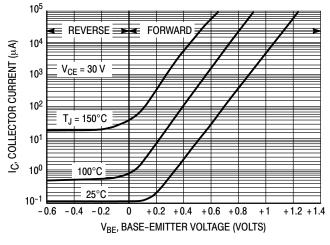


Figure 11. Collector Cut-Off Region

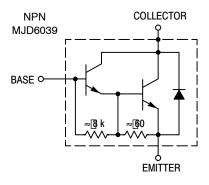
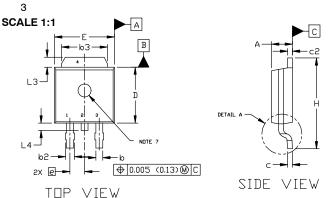


Figure 12. Darlington Schematic

## **DPAK (SINGLE GAUGE)**

CASE 369C **ISSUE G** 

**DATE 31 MAY 2023** 

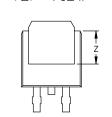


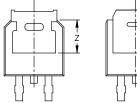


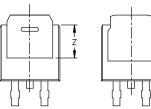
- DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES
- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS 63,
- L3. AND Z. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,
  PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR
  GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
- DIMENSIONS D AND E ARE DETERMINED AT THE DUTERMOST EXTREMES OF THE PLASTIC BODY.

  DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
- OPTIONAL MOLD FEATURE.

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
Α	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
С	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
е	0.090 BSC		2.29 BSC	
Н	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90	REF
L2	0.020 BSC		0.51	BSC
L3	0.035	0.050	0.89	1.27
L4		0.040		1.01
Z	0.155		3.93	





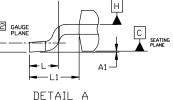


BOTTOM VIEW

5.80

BOTTOM VIEW ALTERNATE

CONSTRUCTIONS [0.228] 6.20 L2 GAUGE PLANE [0.244] 2.58 3.00 [0.102] [0.118] 1.60 [0.063] 6.17



STYLE 5: PIN 1. GATE

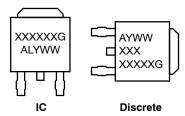
2. ANODE

3 CATHODE

ANODE

CW ROTATED 90°

#### **GENERIC MARKING DIAGRAM\***



= Device Code
= Assembly Location
= Wafer Lot
= Year
= Work Week
= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT\* \*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DUWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

[0.243]

STYLE 1: PIN 1. BASE STYLE 2: PIN 1. GATE STYLE 3: PIN 1. ANODE STYLE 4: PIN 1. CATHODE 2. COLLECTOR 2. DRAIN 2. CATHODE 2. ANODE 3 SOURCE 3 FMITTER 3 ANODE 3 GATE

COLLECTOR 4. DRAIN 4. CATHODE 4. ANODE STYLE 6: STYLE 7: PIN 1. GATE 2. COLLECTOR STYLE 8: STYLE 9: PIN 1. MT1 2. MT2

STYLE 10: PIN 1. N/C 2. CATHODE 3. ANODE PIN 1. ANODE 2. CATHODE PIN 1. CATHODE 2. ANODE 3 CATHODE 3 FMITTER 3 RESISTOR ADJUST 4. COLLECTOR 4. CATHODE 4. ANODE CATHODE

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON10527D	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1	

onsemi and ONSEMI. are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

3 GATE

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales